

May 1999

BSS84 / BSS110

P-Channel Enhancement Mode Field Effect Transistor

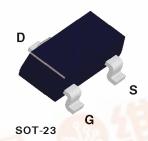
General Description

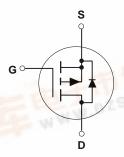
These P-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is designed to minimize on-state resistance, provide rugged and reliable performance and fast switching. They can be used, with a minimum of effort, in most applications requiring up to 0.17A DC and can deliver pulsed currents up to 0.68A. This product is particularly suited to low voltage applications requiring a low current high side switch.

Features

- BSS84: -0.13A, -50V. $R_{\rm DS(ON)} = 10\Omega$ @ $V_{\rm GS} = -5V$. BSS110: -0.17A, -50V. $R_{\rm DS(ON)} = 10\Omega$ @ $V_{\rm GS} = -10V$
- Voltage controlled p-channel small signal switch.
- High density cell design for low R_{DS(ON)}.
- High saturation current.







Absolute Maximum Ratings

T_A = 25°C unless otherwise noted

Symbol	Parameter	BSS84	BSS110	Units		
V _{DSS}	Drain-Source Voltage	-50				
V_{DGR}	Drain-Gate Voltage ($R_{GS} \le 20 \text{ K}\Omega$)	-50				
V_{GSS}	Gate-Source Voltage - Continuous	±20				
I _D	Drain Current - Continuous @ T _A = 30/35°C	-0.13	-0.17	А		
	- Pulsed @ T _A = 25°C	-0.52	-0.68			
P_{D}	Maximum Power Dissipation T _A = 25°C	0.36	0.63	W		
T_J , T_{STG}	Operating and Storage Temperature Range	-55 to 150				
TL	Maximum lead temperature for soldering purposes, 1/16" from case for 10 seconds	300		°C		
THERMA	AL CHARACTERISTICS			•		
P	Thermal Resistance, Junction-to-Ambient	350	200	°C/W		

	RICAL CHARACTERISTICS (T _A = 25°C			_		_		
Symbol	Parameter	Conditions		Type	Min	Тур	Max	Units
OFF CHA	ARACTERISTICS	1				1	1	1
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$		All	-50			V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -50 \text{ V},$	All			-15	μΑ	
		$V_{GS} = 0 V$	T _J = 125°C				-60	μΑ
		$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}$	_s =0 V				-0.1	μΑ
$I_{\rm GSSR}$	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$		All			-10	nA
ON CHA	RACTERISTICS (Note 1)							
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = -1 \text{ mA}$		All	-0.8	-1.75	-2	V
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = -5V, I_{D} = -0.10 A$		BSS84		3.2	10	Ω
		$V_{GS} = -10 \text{ V}, I_D = -0.17 \text{ A}$		BSS110		2.2	10	
g _{FS}	Forward Transconductance	$V_{DS} = -25 \text{ V}, I_{D} = -0.10 \text{A}$		BSS84	0.05	0.27		S
		$V_{DS} = -10 \text{ V}, I_{D} = -0.17 \text{ A}$	BSS110	0.05	0.29			
DYNAMIC	CCHARACTERISTICS	·						
C _{iss}	Input Capacitance	$V_{DS} = -25 \text{ V}, \ V_{GS} = 0 \text{ V}, $ f = 1.0 MHz	BSS84		37	45	pF	
		f = 1.0 MHz	BSS110		37	40		
C _{oss}	Output Capacitance		All		16	25	рF	
C _{rss}	Reverse Transfer Capacitance		All		5	12	рF	
	NG CHARACTERISTICS (Note 1)	-					ı	
t _{D(on)}	Tum - On Delay Time	$V_{DD} = -30 \text{ V}, I_{D} = -0.27 \text{ A},$		All			12	nS
ţ	Turn - On Rise Time	$V_{GS} = -10 \text{ V}, R_{GEN} = 50 \Omega$		All			50	nS
t _{D(off)}	Turn - Off Delay Time			All			10	nS
t,	Turn - Off Fall Time		All			25	nS	
DRAIN-SC	DURCE DIODE CHARACTERISTICS				<u> </u>		I	
I _s	Continuous Source Diode Current		BSS84			-0.13	Α	
3				BSS110			-0.17	
I _{SM}	Maximum Pulsed Source Diode Current	(Note 1)	BSS84			-0.52	Α	
J				BSS110			-0.68	
V_{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -0.26 A (Note 1)	BSS84		-0.95	-1.2	V	
		$V_{GS} = 0 \text{ V}, I_{S} = -0.34 \text{ A} \text{ (Note 1)}$	BSS110		-1	-1.2		

Note: 1. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

Typical Electrical Characteristics

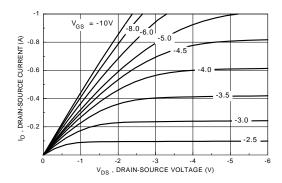


Figure 1. On-Region Characteristics

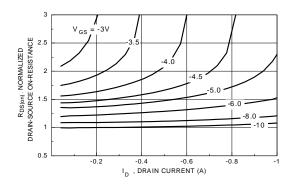


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

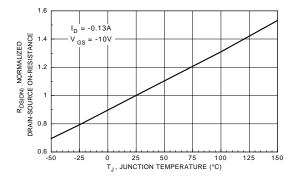


Figure 3. On-Resistance Variation with Temperature

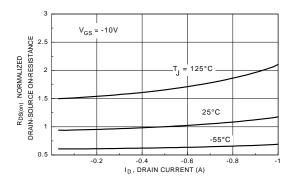


Figure 4. On-Resistance Variation with Drain Current and Temperature

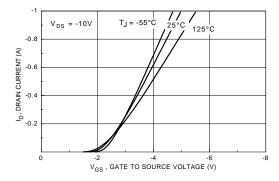


Figure 5. Transfer Characteristics

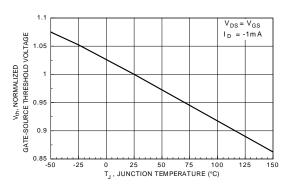


Figure 6. Gate Threshold Variation with Temperature

Typical Electrical Characteristics (continued)

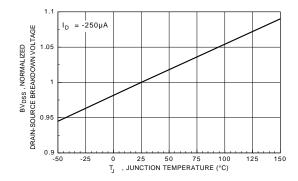


Figure 7. Breakdown Voltage Variation with Temperature

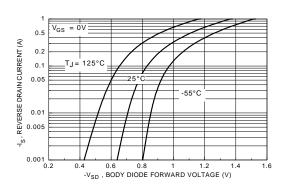


Figure 8. Body Diode Forward Voltage Variation with Source Current and Temperature

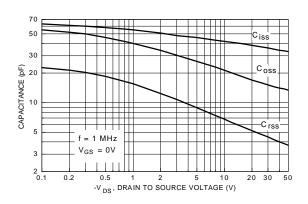


Figure 9. Capacitance Characteristics

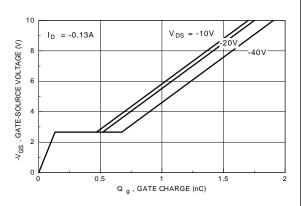


Figure 10. Gate Charge Characteristics

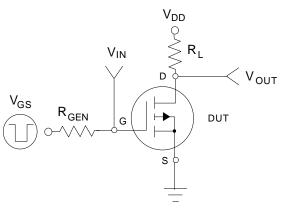


Figure 11. Switching Test Circuit

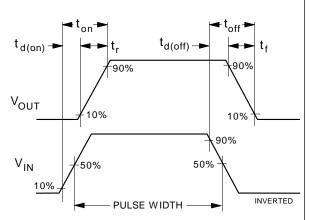
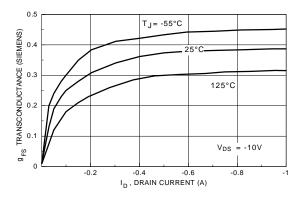


Figure 12. Switching Waveforms

Typical Electrical Characteristics (continued)



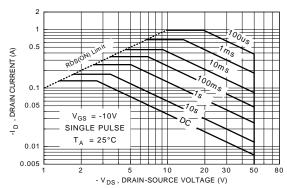


Figure 13. Transconductance Variation with Drain Current and Temperature

Figure 14. Maximum Safe Operating Area

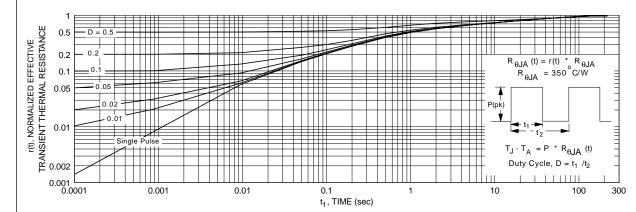


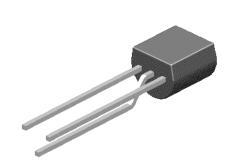
Figure 15. Transient Thermal Response Curve

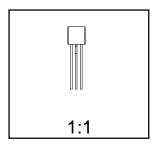
Note: Characterization performed using a circuit board with 175°C/W typical case-to-ambient thermal resistance.

TO-92 Package Dimensions



TO-92; TO-18 Reverse Lead Form (J35Z Option) (FS PKG Code 92, 94, 96)

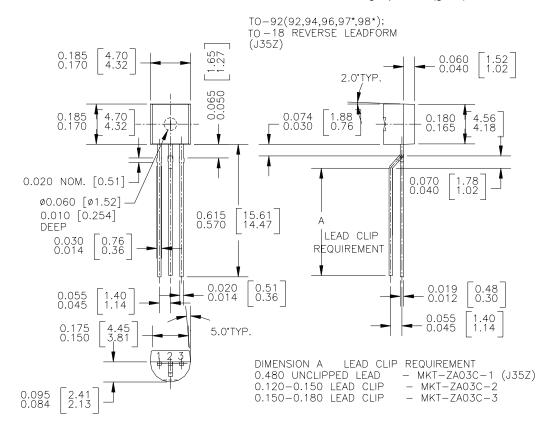




Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.22



Note: All package 97 or 98 transistors are leadformed to this configuration prior to bulk shipment. Order L34Z option if in-line leads are preferred on package 97 or 98.

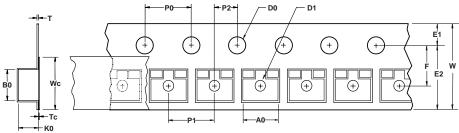
^{*} Standard Option on 97 & 98 package code

SOT-23 Tape and Reel Data and Package Dimensions FAIRCHILD SEMICONDUCTOR TM **SOT-23 Packaging** Configuration: Figure 10 Customized Label Packaging Description: SOT-23 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealart, and arti-static sprayed agent. These reded parts in standard option are shipped with 3000 units per 7 or 177m diameter reel. The reels are dark blue in color ard is made of polystyrene plastic (antisate coated). Other option comes in 10,000 units per 13' or 330cm diameter reel. This and some other options are described in the Packaging Information table. Antistatic Cover Tape These full reads are individually labeled and placed inside a sandard intermedate made of recydable corrugated brown pager with a Farchiel loop portifulty. One pizza box contains eight reals meximum. And these intermedate boxes are placed inside a labeled shipping box which comes in different sizes depending on he number of pats skinned. Human Readable shipped. Embossed Label Carrier Tape 3P SOT-23 Packaging Information Standard Packaging Option D87Z **SOT-23 Unit Orientation** TNR Packagingtype TNR Qty per Reel/Tube/Bag 3.000 10.000 Reel Size 7" Dia 13" Box Dimension (mm) 187x107x183 343x343x64 Human Readable Label 343mm x 342mm x 64mm Max qty per Box 24,000 30,000 Intermedate box for L87Z Option Weight per unit (gm) 0.0082 0.0082 Weight per Reel (kg) 0.1175 0.4006 Note/Comments Human Readable Label sample FAIRCHILD LD. REV D B92022C D729 Lot UG2 5093019 Human readable Label 187mm x 107mm x 183mm **SOT-23 Tape Leader and Trailer** Intermedate Box for Standard Option Configuration: Figure 20 0 0 0 0 0 Components Cover Tape Trailer Tape 300mm minimum or Leader Tape 500mm minimum or 125 empty pockets 75 empty pockets

SOT-23 Tape and Reel Data and Package Dimensions, continued

SOT-23 Embossed Carrier Tape

Configuration: Figure 3.0



User Direction of Feed

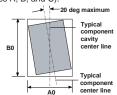
	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

13" Diameter Option



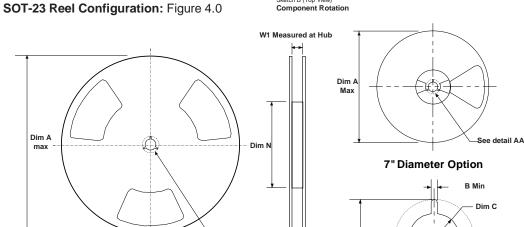
Sketch B (Top View)

Component Rotation



Sketch C (Top View)

Component lateral movement

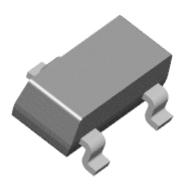


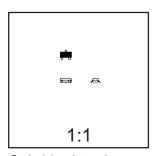
								DETAIL AA	1
	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

W2 max Measured at Hub

SOT-23 Tape and Reel Data and Package Dimensions, continued

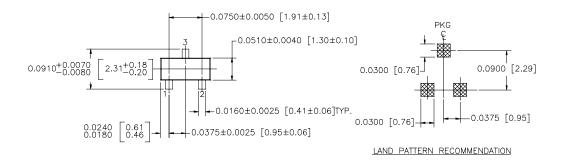
SOT-23 (FS PKG Code 49)

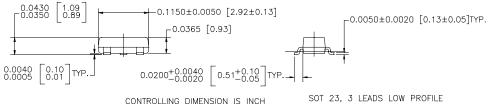




Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0082





CONTROLLING DIMENSION IS INCH VALUES IN [] ARE MILLIMETERS

NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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